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Substitute for Form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Complete If Known	
				Application Number	
				Filing Date	
				First Named Inventor	Chambers et al.
				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket No.	TI-36030

U.S. PATENT DOCUMENTS						
Exam. Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm- dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
Al	AA	5,804,848		Mukai	09/08/1998	Entire Document
Al	AB	5,899,710		Mukai	05/04/1999	Entire Document
Al	AC	2003/0136963	A1	Krivokapic et al.	07/24/2003	Entire Document
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	AE					

FOREIGN PATENT DOCUMENTS							
Exam. Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS						
Exam. Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T <sup>2</sup>
Al	CA	"25nm CMOS Omega FETs", IEEE, FU-LIANG YANG, HAO-YU CHEN, FANG-CHENG CHEN, CHANG-CHUAN HUANG, CHANG-YUN CHANG, HSIEN-KRANG CHIU, CHI-CHUANG LEE, CHI-CHUN CHEN, HUAN-TSUANG HUANG, CHIH-JIAN CHEN HUN-JAN TAO, YEE-CHIA YEO, MONG-SONG LIANG and CHENMING HU, 2002, 4 pgs.				
Al	CB	"SOI Devices for Sub-0.1 μm Gate Lengths", PROC. 23 <sup>rd</sup> International Conference on Microelectronics (Miel 2002), Vol 1, NIS, Yugoslavia, May 12-15, 2002, J.P. COLINGE, J.T. PARK and C.A. COLINGE, pp. 109-113.				
Al	CC	"Advanced Depleted-Substrate Transistors: Single-Gate, Double-Gate and Tri-Gate", 2002 International Conference on Solid State Devices and Materials (SSDM 2002, Nagoya, Japan, ROBERT CHAU, BRIAN DOYLE, JACK KAVALIEROS, DOUGLAS BARLAGE, ANAND MURTHY, MARK DOCZY, RAFAIL RIOS, TOM LINTON, REZA ARGHAVANI, BEN JIN, SUMAN DATTA and SCOTT HARELAND, pp.1-23.				
Al	CD	"Beyond the Conventional Transistor", IBM J. Res. & Dev., Vol. 46, No. 2/3, March/May 2002, H.-S.P. WONG, PP. 133-168.				
	CE					
	CF					
	CG					
	CH					

Examiner Signature	<i>Andy Nease</i>	Date Considered	03/12/05
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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